

# TIC126A, TIC126B, TIC126C, TIC126D, TIC126E, TIC126M, TIC126N, TIC126S

## **P-N-P-N SILICON REVERSE-BLOCKING TRIODE THYRISTORS**

- 12 A Continuous On-State Current
- 100 A Surge-Current
- Glass Passivated Wafer
- 100 V to 800 V Off-State Voltage
- Max I<sub>GT</sub> of 20 mA
- Compliance to ROHS

#### ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value							
		Α	В	С	D	Е	М	S	Ν	
V <sub>DRM</sub>	Repetitive peak off-state voltage (see Note1)	100	200	300	400	500	600	700	800	V
V <sub>RRM</sub>	Repetitive peak reverse voltage	100	200	300	400	500	600	700	800	V
I <sub>T(RMS)</sub>	Continuous on-state current at (or below) 70°C case temperature (see note2)	12						А		
I <sub>T(AV)</sub>	Average on-state current (180° conduction angle) at(or below) 70°C case temperature (see Note3)7.5				А					
I <sub>TM</sub>	Surge on-state current (see Note4)	100							Α	
I <sub>GM</sub>	Peak positive gate current (pulse width ≤300 µs) 3					А				
Р <sub>GM</sub>	Peak power dissipation (pulse width ≤300 5					W				
P <sub>G(AV)</sub>	Average gate power dissipation (see 1 Note5)			1				W		
T <sub>c</sub>	Operating case temperature range	-40 to +110							С°	
T <sub>stg</sub>	Storage temperature range	-40 to +125						°C		
TL	Lead temperature 1.6 mm from case for 10 seconds	230						°C		

Notes:

1. These values apply when the gate-cathode resistance  $R_{GK} = 1k\Omega$ 

2. These values apply for continuous dc operation with resistive load. Above 70°C derate linearly to zero at 110°C.

3. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 70°C derate linearly to zero at 110°C.

4. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

5. This value applies for a maximum averaging time of 20 ms.



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### THERMAL CHARACTERISTICS

Symbol		Value	Unit	
t <sub>gt</sub>	Gate-controlled Turn-on time	$V_{AA} = 30 \text{ V}, \text{ R}_{L} = 6 \Omega,$ $R_{GK(eff)} = 100 \Omega, \text{ V}_{in} = 20 \text{ V}$	0.8	
t <sub>q</sub>	Circuit-communicated Turn-off time	$V_{AA} = 30 \text{ V}, \text{ R}_{L} = 6 \Omega, \text{ I}_{RM} \approx 10 \text{ A}$	11	μs
R∂JC			≤ 2.4	°C/W
R∂JA			≤ 62.5	C/ W

### **ELECTRICAL CHARACTERISTICS**

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Тур	Мx	Unit
I <sub>DRM</sub>	Repetitive peak off-state current	$V_D$ = Rated $V_{DRM}$ , $R_{GK}$ = 1 k $\Omega$ , T <sub>C</sub> = 110°C	-	-	2	mA
I <sub>RRM</sub>	Repetitive peak reverse current	$V_R$ = Rated $V_{RRM}$ , $I_G$ = 0, $T_C$ = 110°C	I	-	2	mA
I <sub>GT</sub>	Gate trigger current	V <sub>AA</sub> = 6 V, R <sub>L</sub> = 100 Ω, t <sub>p(g)</sub> ≥ 20µs	-	5	20	mA
V <sub>GT</sub>	Gate trigger voltage	$V_{AA}$ = 6 V, R <sub>L</sub> = 100 Ω, R <sub>GK</sub> = 1 kΩ, t <sub>p(g)</sub> ≥ 20µs, T <sub>C</sub> = -40°C	-	-	2.5	
		V <sub>AA</sub> = 6 V, R <sub>L</sub> = 100 Ω, R <sub>GK</sub> = 1 kΩ, t <sub>p(g)</sub> ≥ 20μs,	- 0.8		1.5	V
		$V_{AA}$ = 6 V, R <sub>L</sub> = 100 Ω, R <sub>GK</sub> = 1 kΩ, t <sub>p(g)</sub> ≥ 20µs, T <sub>C</sub> = 110°C	0.2	-	-	
I <sub>H</sub>	Holding current	$\label{eq:VAA} \begin{array}{llllllllllllllllllllllllllllllllllll$	-	-	40	
		$V_{AA} = 6 \text{ V}, \text{ R}_{GK} = 1 \text{ k}\Omega,$ initiating I <sub>T</sub> = 100 mA, T <sub>C</sub> = -40°C	-	-	70	mA
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> = 8A (see Note6)	-	-	1.4	V
dv/dt	Critical rate of rise of off-state voltage	$V_D$ = Rated $V_D$ , $T_C$ = 110°C	-	100	-	V/µs

Note 6:

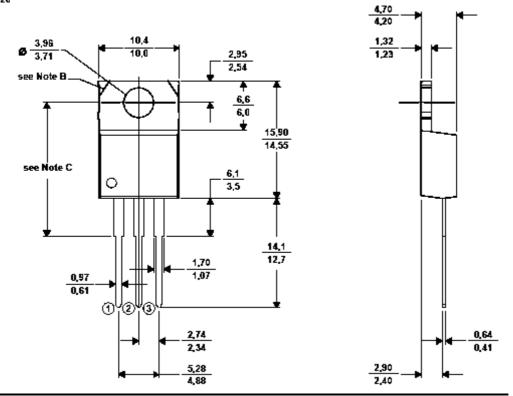
This parameters must be measured using pulse techniques,  $t_W = 300 \mu s$ , duty cycle  $\leq 2 \%$ , voltage-sensing contacts, separate from the courrent-carrying contacts, are located within 3.2mm (1/8 inch) from de device body.

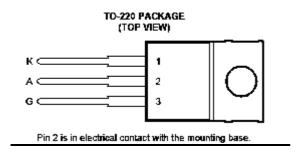


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#### **MECHANICAL DATA CASE TO-220**

TO220





Pin 1 :	kathode
Pin 2 :	Anode
Pin 3 :	Gate